



Effect of Cryo-Quench on the Microstructure of Copper

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Microstructures of materials can determine macroscopic applications

- Copper is an essential interconnect in the semiconductor industry
- Nanocrystalline metals exhibit a promising combinations of conductivity, strength, and ductility[1]
- Refining the microstructure of materials via thermomechanical processing
 - Hot and cold rolling
 - Forging and Extrusion
- Disadvantages include:
 - Extreme heat and pressure systems with large power consumption
 - Cannot be applied to device manufacturing

Why cryogenic treatment?

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- Electronic packaging and semiconductor manipulation cannot be exposed to heavy deformation
- Quantum computers with quantum bits function at temperatures near zero Kelvin[2]
- How do cryogenic environments affect the microstructure and properties of materials, specifically for application in future computing systems?



Materials

- 1. Bulk Copper
 - Diamond cut from copper ring
- 2. Microchip
 - Copper and tin interconnect







Preparation and experiment

- Tube Furnace
 - Annealed bulk copper at 750 °C for two hours
 - Re-annealed after quench at 100 °C for three minutes
- Hitachi IM4000 Plus
 - Milled in two consecutive 45-minute sessions
- Cryo-Quench
 - Liquid Nitrogen (-193oC)
 - Reached steady-state temperature in cryo bath and then dunked in distilled water bath





Liquid Nitrogen Bath





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	No. of Grains	Average Grain Size (μm)
Bulk Copper Basis	150	46.377
Bulk Copper Quenched	147	46.455
Bulk Copper Re-annealed	239	31.384
Cu Microchip Basis	5104	0.740
Cu Microchip Quenched	3840	0.854
Sn Microchip Basis	148	2.893
Sn Microchip Quenched	245	2.093

Average grain size in bulk copper decreased by 32% after re-annealing

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750°C/2h



750°C/2h + -193°C/sec

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750°C/2h + -193°C/sec + 100°C/3min

Local misorientation maps indicate sites of deformation



750°C/2h + -193°C/sec





Microchip before and after cryo-quench

Copper Component on Microchip



Tin Component on Microchip







Forescatter diode (FSD) image of computer chip basis



FSD image of computer chip site after quenching

Tin has a greater thermal expansion coefficient than copper



Water Bath induced compressive stress



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J.-H. Shim, C.-S. Oh, B.-J. Lee and D.N. Lee, Z. "Phase Diagram and Computational Thermodhnamics" $\it Metallkde$

Phase diagram of Sn and Copper

Deformation observed in tin may have led to average grain size reduction





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Local misorientation map of computer chip before quenching

Local misorientation map of computer chip after quenching

To be determined...

- Insufficient driving force
- Re-annealing may release stress and cause recrystallization
- Residue stress analysis
 X-ray diffraction
- Thermal analysis



N. J. Simon, E. S. Drexler, and R. P. Reed "Properties of Copper and Copper Alloys at Cryogenic Temperatures." *International Copper Association, Ltd,*





- Bulk Copper
 - ♦ Avg. grain size increased by <1%
 - After re-annealing avg. grain size decreased by 32%
- Microchip
 - ✤ Cu avg. grain size increased by 15%
 - ✤ Sn avg. grain size decreased by 27%



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